TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPC8061-H**

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 3.5 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS}$  (ON) = 21 m $\Omega$  (typ.) (VGS = 4.5 V)

- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 30 V)$
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V (VDS} = 10 \text{ V, ID} = 0.1 \text{ mA)}$

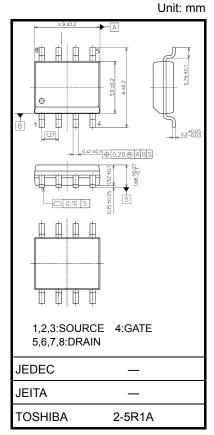
#### **Absolute Maximum Ratings (Ta = 25°C)**

| Characte                | ristic                       | Symbol           | Rating     | Unit |
|-------------------------|------------------------------|------------------|------------|------|
| Drain-source voltage    |                              | $V_{DSS}$        | 30         | V    |
| Drain-gate voltage (R   | GS = 20 kΩ)                  | $V_{DGR}$        | 30         | V    |
| Gate-source voltage     |                              | V <sub>GSS</sub> | ±20        | V    |
| Drain current           | DC (Note 1)                  | ID               | 8          | Α    |
| Diam current            | Pulsed (Note 1)              | $I_{DP}$         | 32         | A    |
| Drain power dissipation | on $(t = 10 s)$<br>(Note 2a) | $P_{D}$          | 1.9        | W    |
| Drain power dissipation | on (t = 10 s)<br>(Note 2b)   | P <sub>D</sub>   | 1.0        | W    |
| Single pulse avalanch   | ne energy<br>(Note 3)        | E <sub>AS</sub>  | 42         | mJ   |
| Avalanche current       |                              | I <sub>AR</sub>  | 8          | Α    |
| Repetitive avalanche    | energy<br>Note 2a) (Note 4)  | E <sub>AR</sub>  | 0.21       | mJ   |
| Channel temperature     |                              | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature     | range                        | T <sub>stg</sub> | -55 to 150 | °C   |

Note: For Notes 1 to 4, refer to the next page.

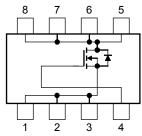
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.085 g (typ.)

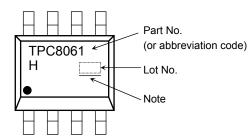
### **Circuit Configuration**



#### **Thermal Characteristics**

| Characteristic                                              | Symbol                 | Max  | Unit |
|-------------------------------------------------------------|------------------------|------|------|
| Thermal resistance, channel to ambient (t = 10 s) (Note 2a) | R <sub>th (ch-a)</sub> | 65.8 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2b) | R <sub>th (ch-a)</sub> | 125  | °C/W |

#### Marking (Note 5)



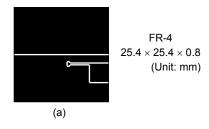
Note: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

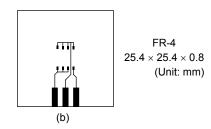
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

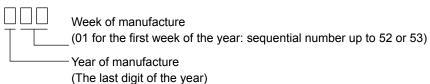




Note 3: 
$$V_{DD} = 24~V$$
,  $T_{ch} = 25^{\circ}C$  (initial),  $L = 500~\mu H$ ,  $R_G = 25~\Omega$ ,  $I_{AR} = 8~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



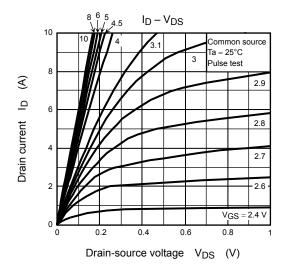
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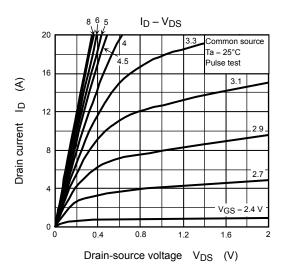
## **Electrical Characteristics (Ta = 25°C)**

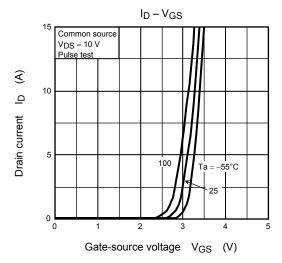
| Characteristic                                     |                    | Symbol               | Test Condition                                                           | Min | Тур. | Max  | Unit |
|----------------------------------------------------|--------------------|----------------------|--------------------------------------------------------------------------|-----|------|------|------|
| Gate leakage cui                                   | rent               | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                        | _   | _    | ±100 | nA   |
| Drain cutoff curre                                 | ent                | I <sub>DSS</sub>     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                            | 10  |      | 10   | μА   |
| Drain-source bre                                   | akdown voltage     | V (BR) DSS           | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ 30                           | 30  | _    | _    | V    |
| Drain-source breakdown voltage                     |                    | V (BR) DSX           | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                            | 15  | _    | _    | V    |
| Gate threshold ve                                  | oltage             | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, I_{D} = 0.1 \text{ mA}$                          | 1.3 | _    | 2.3  | ٧    |
| Drain-source ON-resistance                         |                    | Pro (OV)             | $V_{GS} = 4.5 \text{ V}, I_D = 4 \text{ A}$                              | _   | 21   | 29   | - mΩ |
|                                                    |                    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A                             | _   | 18   | 26   |      |
| Input capacitance                                  |                    | C <sub>iss</sub>     |                                                                          | _   | 630  | _    | pF   |
| Reverse transfer capacitance                       |                    | C <sub>rss</sub>     | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$         | _   | 46   | _    |      |
| Output capacitance                                 |                    | Coss                 |                                                                          | _   | 150  | _    |      |
| Gate resistance                                    |                    | rg                   | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz                 | _   | 1.4  | _    | Ω    |
| Switching time                                     | Rise time          | t <sub>r</sub>       | V <sub>GS</sub> 10 V                                                     | _   | 2.6  | _    | - ns |
|                                                    | Turn-on time       | t <sub>on</sub>      |                                                                          | _   | 7.6  | _    |      |
|                                                    | Fall time          | t <sub>f</sub>       |                                                                          | _   | 2.9  | _    |      |
|                                                    | Turn-off time      | t <sub>off</sub>     | V <sub>DD</sub> ≈ 15 V<br>Duty ≤ 1%, t <sub>W</sub> = 10 μs              | _   | 18   | _    |      |
| Total gate charge<br>(gate-source plus gate-drain) |                    | Qg                   | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$  | _   | 11   | _    |      |
|                                                    |                    |                      | $V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 8 \text{ A}$ | _   | 6.2  | _    | nC   |
| Gate-source charge 1                               |                    | Q <sub>gs1</sub>     | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$  | _   | 2.3  | _    |      |
| Gate-drain ("miller") charge                       |                    | Q <sub>gd</sub>      |                                                                          | _   | 2.5  | _    |      |
| Gate switch char                                   | Gate switch charge |                      |                                                                          | _   | 3.5  | _    |      |

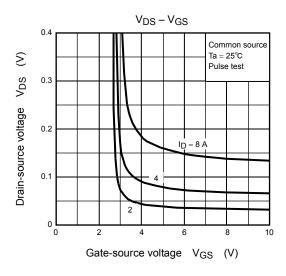
### Source-Drain Ratings and Characteristics (Ta = 25°C)

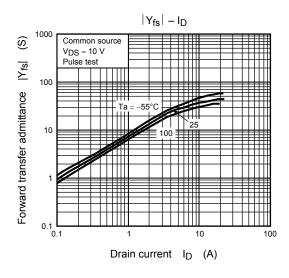
| Characteristics         |       | Symbol   | Test Condition   | Min                                          | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|----------------------------------------------|------|-----|------|---|
| Drain reverse current   | Pulse | (Note 1) | I <sub>DRP</sub> | _                                            | _    | _   | 32   | Α |
| Forward voltage (diode) |       |          | $V_{DSF}$        | I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V | _    | _   | -1.2 | V |

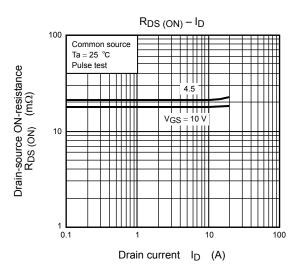


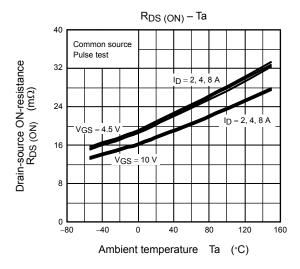


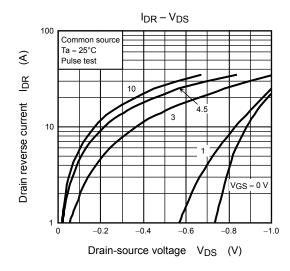


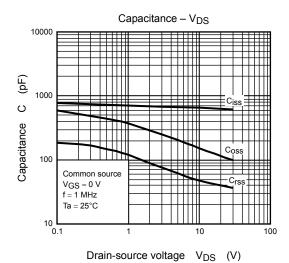


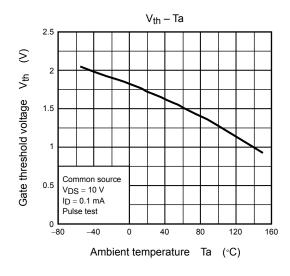


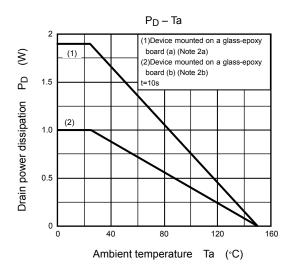


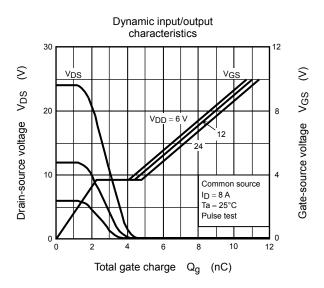


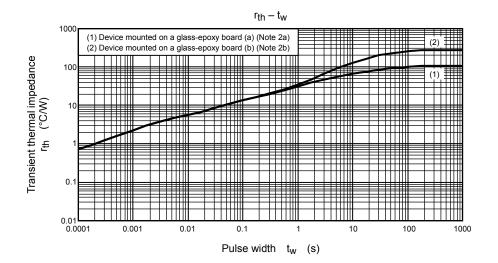


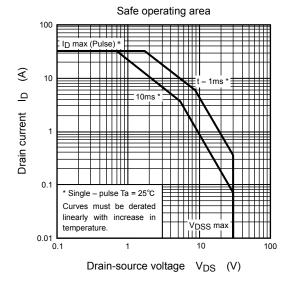












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